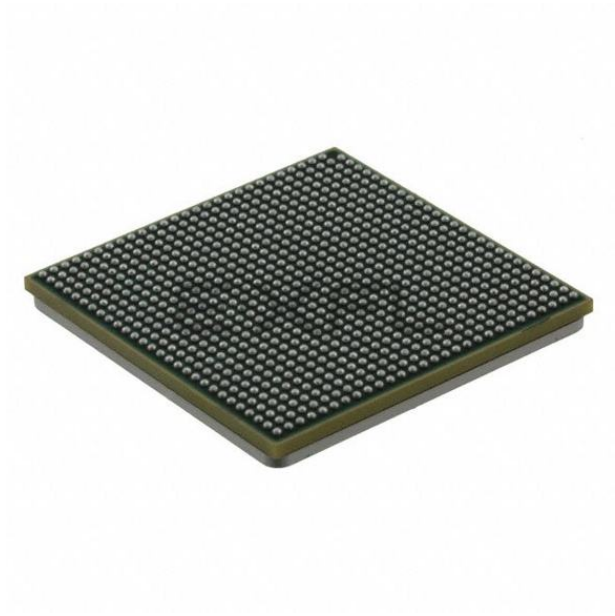

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	533MHz
Co-Processors/DSP	-
RAM Controllers	DDR, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	-
Voltage - I/O	2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8541pxajd

  - Four global high resolution timers/counters that can generate interrupts
  - Supports additional internal interrupt sources
  - Supports fully nested interrupt delivery
  - Interrupts can be routed to external pin for external processing
  - Interrupts can be routed to the e500 core's standard or critical interrupt inputs
  - Interrupt summary registers allow fast identification of interrupt source
- Two I^2C controllers (one is contained within the CPM, the other is a stand-alone controller which is not part of the CPM)
  - Two-wire interface
  - Multiple master support
  - Master or slave I^2C mode support
  - On-chip digital filtering rejects spikes on the bus
- Boot sequencer
  - Optionally loads configuration data from serial ROM at reset via the stand-alone I^2C interface
  - Can be used to initialize configuration registers and/or memory
  - Supports extended I^2C addressing mode
  - Data integrity checked with preamble signature and CRC
- DUART
  - Two 4-wire interfaces (RXD, TXD, RTS, CTS)
  - Programming model compatible with the original 16450 UART and the PC16550D
- Local bus controller (LBC)
  - Multiplexed 32-bit address and data operating at up to 166 MHz
  - Eight chip selects support eight external slaves
  - Up to eight-beat burst transfers
  - The 32-, 16-, and 8-bit port sizes are controlled by an on-chip memory controller
  - Three protocol engines available on a per chip select basis:
    - General purpose chip select machine (GPCM)
    - Three user programmable machines (UPMs)
    - Dedicated single data rate SDRAM controller
  - Parity support
  - Default boot ROM chip select with configurable bus width (8-, 16-, or 32-bit)
- Two Three-speed (10/100/1000)Ethernet controllers (TSECs)
  - Dual IEEE 802.3, 802.3u, 802.3x, 802.3z AC compliant controllers
  - Support for Ethernet physical interfaces:
    - 10/100/1000 Mbps IEEE 802.3 GMII
    - 10/100 Mbps IEEE 802.3 MII
    - 10 Mbps IEEE 802.3 MII

Figure 3 shows the undershoot and overshoot voltage of the PCI interface of the MPC8541E for the 3.3-V signals, respectively.

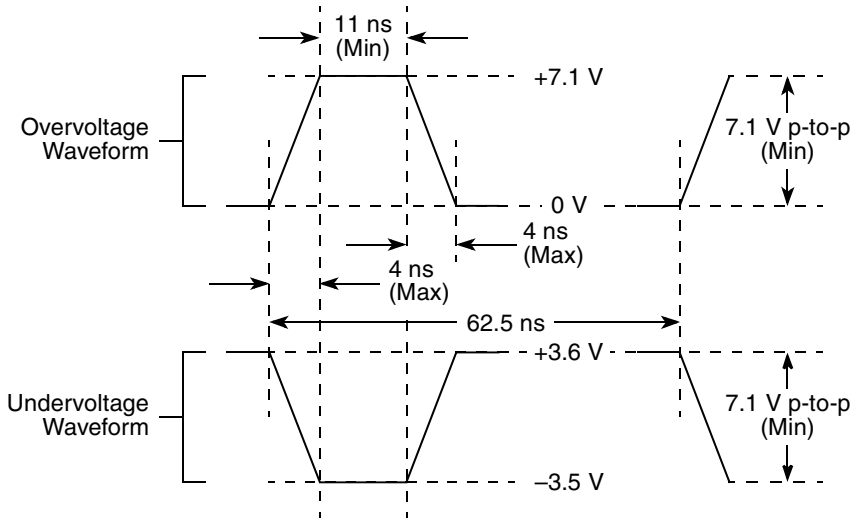


Figure 3. Maximum AC Waveforms on PCI interface for 3.3-V Signaling

2.1.4 Output Driver Characteristics

Table 3 provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 3. Output Drive Capability

Driver Type	Programmable Output Impedance (Ω)	Supply Voltage	Notes
Local bus interface utilities signals	25	OV_{DD} = 3.3 V	1
	42 (default)		
PCI signals	25		2
	42 (default)		
DDR signal	20	GV_{DD} = 2.5 V	
TSEC/10/100 signals	42	LV_{DD} = 2.5/3.3 V	
DUART, system control, I2C, JTAG	42	OV_{DD} = 3.3 V	

Notes:
1. The drive strength of the local bus interface is determined by the configuration of the appropriate bits in PORIMPSCR.
2. The drive strength of the PCI interface is determined by the setting of the $\overline{\text{PCI\_GNT1}}$ signal at reset.

3 Power Characteristics

The estimated typical power dissipation for this family of PowerQUICC III devices is shown in Table 4.

Table 4. Power Dissipation(1) (2)

CCB Frequency (MHz)	Core Frequency (MHz)	V_{DD}	Typical Power(3)(4) (W)	Maximum Power(5) (W)
200	400	1.2	4.4	6.1
	500	1.2	4.7	6.5
	600	1.2	5.0	6.8
267	533	1.2	4.9	6.7
	667	1.2	5.4	7.2
	800	1.2	5.8	8.6
333	667	1.2	5.5	7.4
	833	1.2	6.0	8.8
	1000(6)	1.3	9.0	12.2

Notes:

1. The values do not include I/O supply power (OV_{DD}, LV_{DD}, GV_{DD}) or AV_{DD}.
2. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance. Any customer design must take these considerations into account to ensure the maximum 105 degrees junction temperature is not exceeded on this device.
3. Typical power is based on a nominal voltage of V_{DD} = 1.2V, a nominal process, a junction temperature of T_j = 105° C, and a Dhrystone 2.1 benchmark application.
4. Thermal solutions likely need to design to a value higher than Typical Power based on the end application, T_A target, and I/O power
5. Maximum power is based on a nominal voltage of V_{DD} = 1.2V, worst case process, a junction temperature of T_j = 105° C, and an artificial smoke test.
6. The nominal recommended V_{DD} = 1.3V for this speed grade.

Notes:

1.

2.

3.

4.

5.

6.

Table 5. Typical I/O Power Dissipation

Interface	Parameters	GV_{DD} (2.5 V)	OV_{DD} (3.3 V)	LV_{DD} (3.3 V)	LV_{DD} (2.5 V)	Unit	Comments
DDR I/O	CCB = 200 MHz	0.46	—	—	—	W	—
	CCB = 266 MHz	0.59	—	—	—	W	—
	CCB = 300 MHz	0.66	—	—	—	W	—
	CCB = 333 MHz	0.73	—	—	—	W	—
PCI I/O	64b, 66 MHz	—	0.14	—	—	W	—
	64b, 33 MHz	—	0.08	—	—	W	—
	32b, 66 MHz	—	0.07	—	—	W	Multiply by 2 if using two 32b ports
	32b, 33 MHz	—	0.04	—	—	W	
Local Bus I/O	32b, 167 MHz	—	0.30	—	—	W	—
	32b, 133 MHz	—	0.24	—	—	W	—
	32b, 83 MHz	—	0.16	—	—	W	—
	32b, 66 MHz	—	0.13	—	—	W	—
	32b, 33 MHz	—	0.07	—	—	W	—
TSEC I/O	MII	—	—	0.01	—	W	Multiply by number of interfaces used.
	GMII or TBI	—	—	0.07	—	W	
	RGMII or RTBI	—	—	—	0.04	W	
CPM - FCC	MII	—	0.015	—	—	W	—
	RMII	—	0.013	—	—	W	—
	HDLC 16 Mbps	—	0.009	—	—	W	—

6 DDR SDRAM

This section describes the DC and AC electrical specifications for the DDR SDRAM interface of the MPC8541E.

6.1 DDR SDRAM DC Electrical Characteristics

Table 11 provides the recommended operating conditions for the DDR SDRAM component(s) of the MPC8541E.

Table 11. DDR SDRAM DC Electrical Characteristics

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.18$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	–0.3	$MV_{REF} - 0.18$	V	—
Output leakage current	I_{OZ}	–10	10	µA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–15.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	15.2	—	mA	—
MV_{REF} input leakage current	I_{VREF}	—	5	µA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, $0 V \le V_{OUT} \le GV_{DD}$.

Table 12 provides the DDR capacitance.

Table 12. DDR SDRAM Capacitance

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, MSYNC_IN	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak to peak) = 0.2 V.

8.2.3 MII AC Timing Specifications

This section describes the MII transmit and receive AC timing specifications.

8.2.3.1 MII Transmit AC Timing Specifications

Table 22 provides the MII transmit AC timing specifications.

Table 22. MII Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD} of 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
TX_CLK clock period 10 Mbps	t_{MTX}[2]	—	400	—	ns
TX_CLK clock period 100 Mbps	t_{MTX}	—	40	—	ns
TX_CLK duty cycle	t_{MTXH}/t_{MTX}	35	—	65	%
TX_CLK to MII data TXD[3:0], TX_ER, TX_EN delay	t_{MTKHDX}	1	5	15	ns
TX_CLK data clock rise and fall time	t_{MTXR}, t_{MTXF} [2,3]	1.0	—	4.0	ns

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Signal timings are measured at 0.7 V and 1.9 V voltage levels.
3. Guaranteed by design.

Figure 10 shows the MII transmit AC timing diagram.

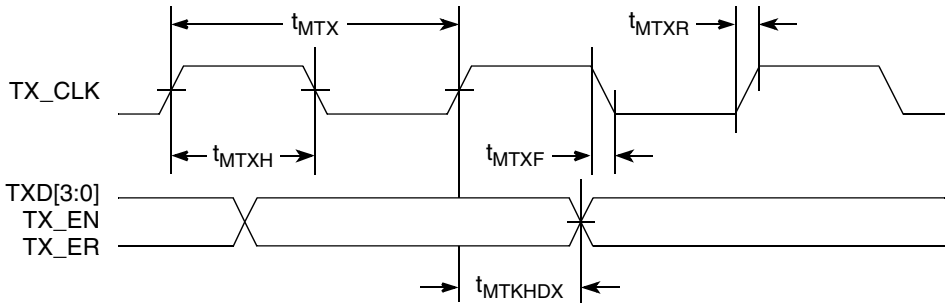


Figure 10. MII Transmit AC Timing Diagram

10 CPM

This section describes the DC and AC electrical specifications for the CPM of the MPC8541E.

10.1 CPM DC Electrical Characteristics

Table 32 provides the DC electrical characteristics for the CPM.

Table 32. CPM DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit	Notes
Input high voltage	V_{IH}		2.0	3.465	V	1
Input low voltage	V_{IL}		GND	0.8	V	1, 2
Output high voltage	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V	1
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V	1
Output high voltage	V_{OH}	I_{OH} = –2.0 mA	2.4	—	V	1
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V	1

10.2 CPM AC Timing Specifications

Table 33 and Table 34 provide the CPM input and output AC timing specifications, respectively.

NOTE: Rise/Fall Time on CPM Input Pins

It is recommended that the rise/fall time on CPM input pins should not exceed 5 ns. This should be enforced especially on clock signals. Rise time refers to signal transitions from 10% to 90% of VCC; fall time refers to transitions from 90% to 10% of VCC.

Table 33. CPM Input AC Timing Specifications [1]

Characteristic	Symbol [2]	Min[3]	Unit
FCC inputs—internal clock (NMSI) input setup time	t_{FIIVKH}	6	ns
FCC inputs—internal clock (NMSI) hold time	t_{FIIXKH}	0	ns
FCC inputs—external clock (NMSI) input setup time	t_{FEIVKH}	2.5	ns
FCC inputs—external clock (NMSI) hold time	t_{FEIXKH}b	2	ns
SPI inputs—internal clock (NMSI) input setup time	t_{NIIVKH}	6	ns
SPI inputs—internal clock (NMSI) input hold time	t_{NIIXKH}	0	ns
SPI inputs—external clock (NMSI) input setup time	t_{NEIVKH}	4	ns
SPI inputs—external clock (NMSI) input hold time	t_{NEIXKH}	2	ns
PIO inputs—input setup time	t_{PIIVKH}	8	ns

10.3 CPM I2C AC Specification

Table 35. I2C Timing

Characteristic	Expression	All Frequencies		Unit
		Min	Max	
SCL clock frequency (slave)	f_{SCL}	0	F_{MAX}(1)	Hz
SCL clock frequency (master)	f_{SCL}	BRGCLK/16512	BRGCLK/48	Hz
Bus free time between transmissions	t_{SDHDL}	1/(2.2 * f_{SCL})	—	s
Low period of SCL	t_{SCLCH}	1/(2.2 * f_{SCL})	—	s
High period of SCL	t_{SCHCL}	1/(2.2 * f_{SCL})	—	s
Start condition setup time[2]	t_{SCHDL}	2/(divider * f_{SCL})	(2)	s
Start condition hold time[2]	t_{SDLCL}	3/(divider * f_{SCL})	—	s
Data hold time [2]	t_{SCLDX}	2/(divider * f_{SCL})	—	s
Data setup time[2]	t_{SDVCH}	3/(divider * f_{SCL})	—	s
SDA/SCL rise time	t_{SRISE}	—	1/(10 * f_{SCL})	s
SDA/SCL fall time	t_{SFALL}	—	1/(33 * f_{SCL})	s
Stop condition setup time	t_{SCHDH}	2/(divider * f_{SCL})	—	s

Notes:

1. F_{MAX} = BRGCLK/(min_divider*prescale. Where prescaler=25-I2MODE[PDIV]; and min_divider=12 if digital filter disabled and 18 if enabled.
   Example #1: if I2MODE[PDIV]=11 (prescaler=4) and I2MODE[FLT]=0 (digital filter disabled) then FMAX=BRGCLK/48
   Example #2: if I2MODE[PDIV]=00 (prescaler=32) and I2MODE[FLT]=1 (digital filter enabled) then FMAX=BRGCLK/576
2. divider = f_{SCL}/prescaler.
   In master mode: divider=BRGCLK/(f_{SCL}*prescaler)=2*(I2BRG[DIV]+3)
   In slave mode: divider=BRGCLK/(f_{SCL}*prescaler)

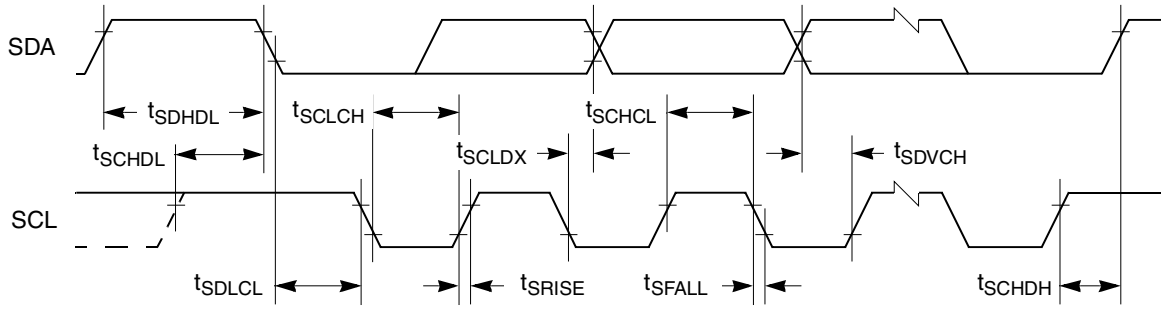


Figure 30. CPM I2C Bus Timing Diagram

The following two tables are examples of I2C AC parameters at I2C clock value of 100k and 400k respectively.

Table 36. CPM I2C Timing (f_{SCL}=100 kHz)

Characteristic	Expression	Frequency = 100 kHz		Unit
		Min	Max	
SCL clock frequency (slave)	f_{SCL}	—	100	kHz
SCL clock frequency (master)	f_{SCL}	—	100	kHz
Bus free time between transmissions	t_{SDHDL}	4.7	—	µs
Low period of SCL	t_{SCLCH}	4.7	—	µs
High period of SCL	t_{SCHCL}	4	—	µs
Start condition setup time	t_{SCHDL}	2	—	µs
Start condition hold time	t_{SDLCL}	3	—	µs
Data hold time	t_{SCLDX}	2	—	µs
Data setup time	t_{SDVCH}	3	—	µs
SDA/SCL rise time	t_{SRISE}	—	1	µs
SDA/SCL fall time (master)	t_{SFALL}	—	303	ns
Stop condition setup time	t_{SCHDH}	2	—	µs

Table 37. CPM I2C Timing (f_{SCL}=400 kHz)

Characteristic	Expression	Frequency = 400 kHz		Unit
		Min	Max	
SCL clock frequency (slave)	f_{SCL}	—	400	kHz
SCL clock frequency (master)	f_{SCL}	—	400	kHz
Bus free time between transmissions	t_{SDHDL}	1.2	—	µs
Low period of SCL	t_{SCLCH}	1.2	—	µs
High period of SCL	t_{SCHCL}	1	—	µs
Start condition setup time	t_{SCHDL}	420	—	ns
Start condition hold time	t_{SDLCL}	630	—	ns
Data hold time	t_{SCLDX}	420	—	ns
Data setup time	t_{SDVCH}	630	—	ns
SDA/SCL rise time	t_{SRISE}	—	250	ns
SDA/SCL fall time	t_{SFALL}	—	75	ns
Stop condition setup time	t_{SCHDH}	420	—	ns

Table 43. MPC8541E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
GND	A12, A17, B3, B14, B20, B26, B27, C2, C4, C11,C17, C19, C22, C27, D8, E3, E12, E24, F11, F18, F23, G9, G12, G25, H4, H12, H14, H17, H20, H22, H27, J19, J24, K5, K9, K18, K23, K28, L6, L20, L25, M4, M12, M14, M16, M22, M27, N2, N13, N15, N17, P12, P14, P16, P23, R13, R15, R17, R20, R26, T3, T8, T10, T12, T14, T16, U6, U13, U15, U16, U17, U21, V7, V10, V26, W5, W18, W23, Y8, Y16, AA6, AA13, AB4, AB11, AB19, AC6, AC9, AD3, AD8, AD17, AF2, AF4, AF10, AF13, AF15, AF27, AG3, AG7	—	—	—
GV_{DD}	A14, A20, A25, A26, A27, A28, B17, B22, B28, C12, C28, D16, D19, D21, D24, D28, E17, E22, F12, F15, F19, F25, G13, G18, G20, G23, G28, H19, H24, J12, J17, J22, J27, K15, K20, K25, L13, L23, L28, M25, N21	Power for DDR DRAM I/O Voltage (2.5 V)	GV_{DD}	—
LV_{DD}	A4, C5, E7, H10	Reference Voltage; Three-Speed Ethernet I/O (2.5 V, 3.3 V)	LV_{DD}	—
MV_{REF}	N27	Reference Voltage Signal; DDR	MV_{REF}	—
No Connects	AA24, AA25, AA3, AA4, AA7 AA8, AB24, AB25, AC24, AC25, AD23, AD24, AD25, AE23, AE24, AE25, AE26, AE27, AF24, AF25, H1, H2, J1, J2, J3, J4, J5, J6, M1, N1, N10, N11, N4, N5, N7, N8, N9, P10, P8, P9, R10, R11, T24, T25, U24, U25, V24, V25, W24, W25, W9, Y24, Y25, Y5, Y6, Y9, AH26, AH28, AG28, AH1, AG1, AH2, B1, B2, A2, A3	—	—	16
OV_{DD}	D1, E4, H3, K4, K10, L7, M5, N3, P22, R19, R25, T2, T7, U5, U20, U26, V8, W4, W13, W19, W21, Y7, Y23, AA5, AA12, AA16, AA20, AB7, AB9, AB26, AC5, AC11, AC17, AD4, AE1, AE8, AE10, AE15, AF7, AF12, AG27, AH4	PCI, 10/100 Ethernet, and other Standard (3.3 V)	OV_{DD}	—
RESERVED	C1, T11, U11, AF1	—	—	15
SENSEVDD	L12	Power for Core (1.2 V)	V_{DD}	13
SENSEVSS	K12	—	—	13
V_{DD}	M13, M15, M17, N14, N16, P13, P15, P17, R12, R14, R16, T13, T15, T17, U12, U14	Power for Core (1.2 V)	V_{DD}	—
CPM				
PA[8:31]	J7, J8, K8, K7, K6, K3, K2, K1, L1, L2, L3, L4, L5, L8, L9, L10, L11, M10, M9, M8, M7, M6, M3, M2	I/0	OV_{DD}	—

15 Clocking

This section describes the PLL configuration of the MPC8541E. Note that the platform clock is identical to the CCB clock.

15.1 Clock Ranges

Table 44 provides the clocking specifications for the processor core and Table 44 provides the clocking specifications for the memory bus.

Table 44. Processor Core Clocking Specifications

Characteristic	Maximum Processor Core Frequency										Unit	Notes
	533 MHz		600 MHz		667 MHz		833 MHz		1000 MHz			
	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
e500 core processor frequency	400	533	400	600	400	667	400	833	400	1000	MHz	1, 2, 3

Notes:

1. **Caution:** The CCB to SYSCLK ratio and e500 core to CCB ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies. Refer to Section 15.2, “Platform/System PLL Ratio,” and Section 15.3, “e500 Core PLL Ratio,” for ratio settings.
2.)The minimum e500 core frequency is based on the minimum platform frequency of 200 MHz.
3. 1000 MHz frequency supports only a 1.3 V core.

Table 45. Memory Bus Clocking Specifications

Characteristic	Maximum Processor Core Frequency		Unit	Notes
	533, 600, 667, 883, 1000 MHz			
	Min	Max		
Memory bus frequency	100	166	MHz	1, 2, 3

Notes:

1. **Caution:** The CCB to SYSCLK ratio and e500 core to CCB ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies. Refer to Section 15.2, “Platform/System PLL Ratio,” and Section 15.3, “e500 Core PLL Ratio,” for ratio settings.
2. The memory bus speed is half of the DDR data rate, hence, half of the platform clock frequency.
3. 1000 MHz frequency supports only a 1.3 V core.

15.2 Platform/System PLL Ratio

The platform clock is the clock that drives the L2 cache, the DDR SDRAM data rate, and the e500 core complex bus (CCB), and is also called the CCB clock. The values are determined by the binary value on LA[28:31] at power up, as shown in Table 46.

There is no default for this PLL ratio; these signals must be pulled to the desired values.

For specifications on the PCI_CLK, refer to the PCI 2.2 Specification.

Table 46. CCB Clock Ratio

Binary Value of LA[28:31] Signals	Ratio Description
0000	16:1 ratio CCB clock: SYSCLK (PCI bus)
0001	Reserved
0010	2:1 ratio CCB clock: SYSCLK (PCI bus)
0011	3:1 ratio CCB clock: SYSCLK (PCI bus)
0100	4:1 ratio CCB clock: SYSCLK (PCI bus)
0101	5:1 ratio CCB clock: SYSCLK (PCI bus)
0110	6:1 ratio CCB clock: SYSCLK (PCI bus)
0111	Reserved
1000	8:1 ratio CCB clock: SYSCLK (PCI bus)
1001	9:1 ratio CCB clock: SYSCLK (PCI bus)
1010	10:1 ratio CCB clock: SYSCLK (PCI bus)
1011	Reserved
1100	12:1 ratio CCB clock: SYSCLK (PCI bus)
1101	Reserved
1110	Reserved
1111	Reserved

16 Thermal

This section describes the thermal specifications of the MPC8541E.

16.1 Thermal Characteristics

Table 49 provides the package thermal characteristics for the MPC8541E.

Table 49. Package Thermal Characteristics

Characteristic	Symbol	Value	Unit	Notes
Junction-to-ambient Natural Convection on four layer board (2s2p)	$R_{\theta JMA}$	17	°C/W	1, 2
Junction-to-ambient (@200 ft/min or 1.0 m/s) on four layer board (2s2p)	$R_{\theta JMA}$	14	°C/W	1, 2
Junction-to-ambient (@400 ft/min or 2.0 m/s) on four layer board (2s2p)	$R_{\theta JMA}$	13	°C/W	1, 2
Junction-to-board thermal	$R_{\theta JB}$	10	°C/W	3
Junction-to-case thermal	$R_{\theta JC}$	0.96	°C/W	4

Notes

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance
2. Per JEDEC JESD51–6 with the board horizontal.
3. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
4. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1). Cold plate temperature is used for case temperature; measured value includes the thermal resistance of the interface layer.

16.2 Thermal Management Information

This section provides thermal management information for the flip chip plastic ball grid array (FC-PBGA) package for air-cooled applications. Proper thermal control design is primarily dependent on the system-level design—the heat sink, airflow, and thermal interface material. The recommended attachment method to the heat sink is illustrated in Figure 42. The heat sink should be attached to the printed-circuit board with the spring force centered over the die. This spring force should not exceed 10 pounds force.

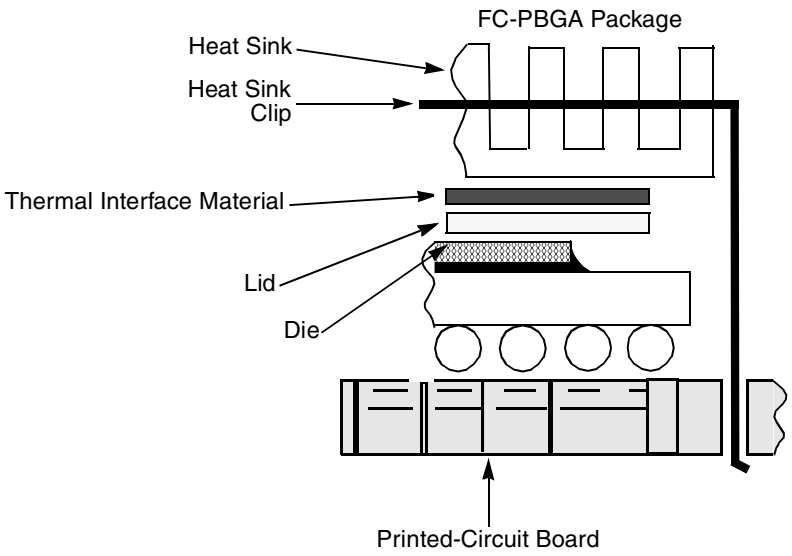


Figure 42. Package Exploded Cross-Sectional View with Several Heat Sink Options

The system board designer can choose between several types of heat sinks to place on the MPC8541E. There are several commercially-available heat sinks from the following vendors:

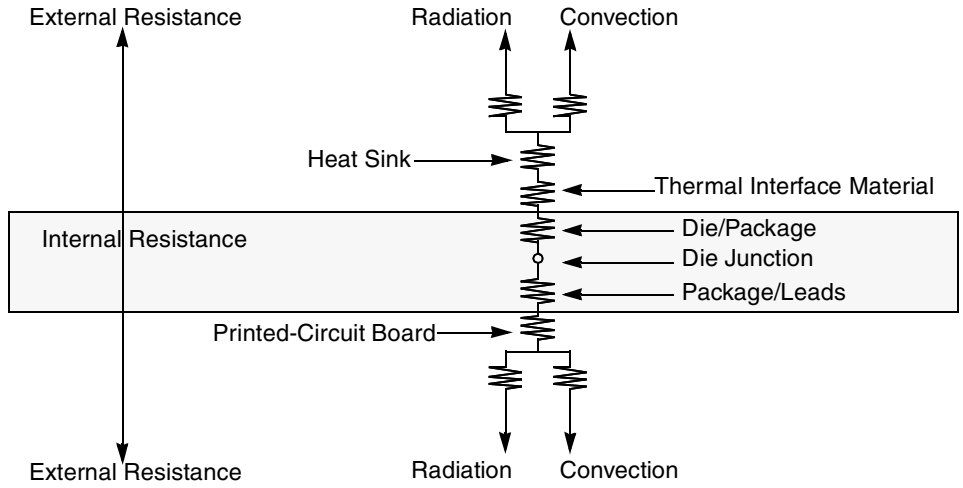
Aavid Thermalloy 80 Commercial St. Concord, NH 03301 Internet: www.aavidthermalloy.com	603-224-9988
Alpha Novatech 473 Sapena Ct. #15 Santa Clara, CA 95054 Internet: www.alphanovatech.com	408-749-7601
International Electronic Research Corporation (IERC) 413 North Moss St. Burbank, CA 91502 Internet: www.ctscorp.com	818-842-7277
Millennium Electronics (MEI) Loroco Sites 671 East Brokaw Road San Jose, CA 95112 Internet: www.mei-millennium.com	408-436-8770
Tyco Electronics Chip Coolers™ P.O. Box 3668 Harrisburg, PA 17105-3668 Internet: www.chipcoolers.com	800-522-6752
Wakefield Engineering 33 Bridge St. Pelham, NH 03076 Internet: www.wakefield.com	603-635-5102

16.2.2 Internal Package Conduction Resistance

For the packaging technology, shown in Table 49, the intrinsic internal conduction thermal resistance paths are as follows:

- The die junction-to-case thermal resistance
- The die junction-to-board thermal resistance

Figure 44 depicts the primary heat transfer path for a package with an attached heat sink mounted to a printed-circuit board.



(Note the internal versus external package resistance)

Figure 44. Package with Heat Sink Mounted to a Printed-Circuit Board

The heat sink removes most of the heat from the device. Heat generated on the active side of the chip is conducted through the silicon and through the lid, then through the heat sink attach material (or thermal interface material), and finally to the heat sink. The junction-to-case thermal resistance is low enough that the heat sink attach material and heat sink thermal resistance are the dominant terms.

16.2.3 Thermal Interface Materials

A thermal interface material is required at the package-to-heat sink interface to minimize the thermal contact resistance. For those applications where the heat sink is attached by spring clip mechanism, Figure 45 shows the thermal performance of three thin-sheet thermal-interface materials (silicone, graphite/oil, floroether oil), a bare joint, and a joint with thermal grease as a function of contact pressure. As shown, the performance of these thermal interface materials improves with increasing contact pressure. The use of thermal grease significantly reduces the interface thermal resistance. The bare joint results in a thermal resistance approximately six times greater than the thermal grease joint.

Heat sinks are attached to the package by means of a spring clip to holes in the printed-circuit board (see Figure 41). Therefore, the synthetic grease offers the best thermal performance, especially at the low interface pressure.

When removing the heat sink for re-work, it is preferable to slide the heat sink off slowly until the thermal interface material loses its grip. If the support fixture around the package prevents sliding off the heat sink,

The spring mounting should be designed to apply the force only directly above the die. By localizing the force, rocking of the heat sink is minimized. One suggested mounting method attaches a plastic fence to the board to provide the structure on which the heat sink spring clips. The plastic fence also provides the opportunity to minimize the holes in the printed-circuit board and to locate them at the corners of the package. Figure 47 and provide exploded views of the plastic fence, heat sink, and spring clip.

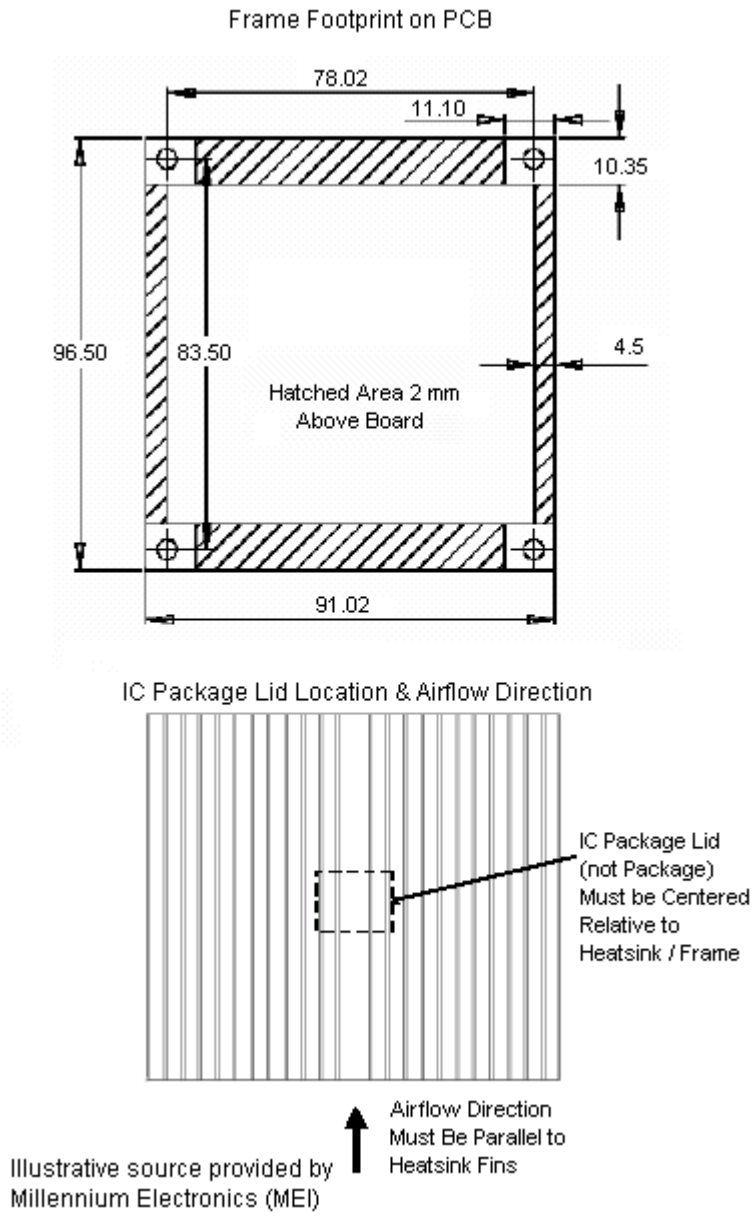
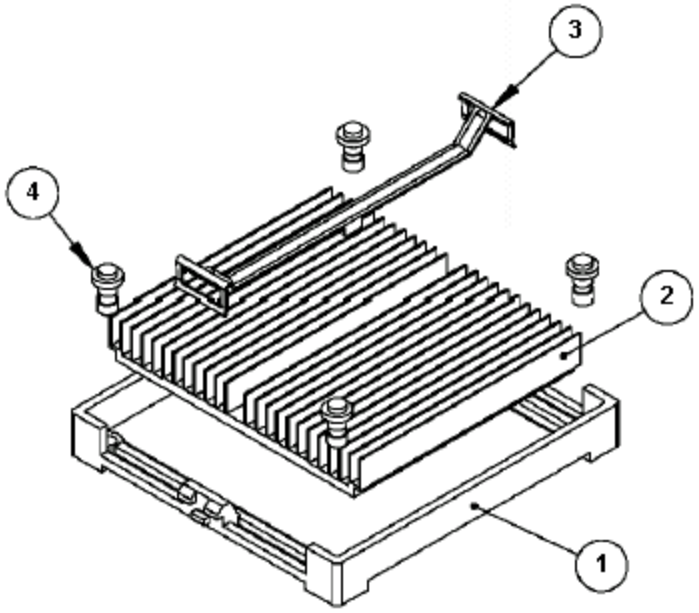


Figure 47. Exploded Views (1) of a Heat Sink Attachment using a Plastic Fence

Item No	QTY	MEI PN	Description
1	1	MFRAME-2000	HEATSINK FRAME
2	1	MSNK-1120	EXTRUDED HEATSINK
3	1	MCLIP-1013	CLIP
4	4	MPPINS-1000	FRAME ATTACHMENT PINS



Illustrative source provided by
Millennium Electronics (MEI)

Figure 48. Exploded Views (2) of a Heat Sink Attachment using a Plastic Force

The die junction-to-ambient and the heat sink-to-ambient thermal resistances are common figure-of-merits used for comparing the thermal performance of various microelectronic packaging technologies, one should exercise caution when only using this metric in determining thermal management because no single parameter can adequately describe three-dimensional heat flow. The final die-junction operating temperature is not only a function of the component-level thermal resistance, but the system level design and its operating conditions. In addition to the component's power consumption, a number of factors affect the final operating die-junction temperature: airflow, board population (local heat flux of adjacent components), system air temperature rise, altitude, etc.

Due to the complexity and the many variations of system-level boundary conditions for today's microelectronic equipment, the combined effects of the heat transfer mechanisms (radiation convection and conduction) may vary widely. For these reasons, we recommend using conjugate heat transfer models for the boards, as well as, system-level designs.

17 System Design Information

This section provides electrical and thermal design recommendations for successful application of the MPC8541E.

17.1 System Clocking

The MPC8541E includes five PLLs.

1. The platform PLL ($AV_{DD}1$) generates the platform clock from the externally supplied SYSCLK input. The frequency ratio between the platform and SYSCLK is selected using the platform PLL ratio configuration bits as described in Section 15.2, "Platform/System PLL Ratio."
2. The e500 Core PLL ($AV_{DD}2$) generates the core clock as a slave to the platform clock. The frequency ratio between the e500 core clock and the platform clock is selected using the e500 PLL ratio configuration bits as described in Section 15.3, "e500 Core PLL Ratio."
3. The CPM PLL ($AV_{DD}3$) is slaved to the platform clock and is used to generate clocks used internally by the CPM block. The ratio between the CPM PLL and the platform clock is fixed and not under user control.
4. The PCI1 PLL ($AV_{DD}4$) generates the clocking for the first PCI bus.
5. The PCI2 PLL ($AV_{DD}5$) generates the clock for the second PCI bus.

17.2 PLL Power Supply Filtering

Each of the PLLs listed above is provided with power through independent power supply pins ($AV_{DD}1$, $AV_{DD}2$, $AV_{DD}3$, $AV_{DD}4$, and $AV_{DD}5$ respectively). The AV_{DD} level should always be equivalent to V_{DD}, and preferably these voltages are derived directly from V_{DD} through a low frequency filter scheme such as the following.

There are a number of ways to reliably provide power to the PLLs, but the recommended solution is to provide five independent filter circuits as illustrated in Figure 49, one to each of the five AV_{DD} pins. By providing independent filters to each PLL the opportunity to cause noise injection from one PLL to the other is reduced.

This circuit is intended to filter noise in the PLLs resonant frequency range from a 500 kHz to 10 MHz range. It should be built with surface mount capacitors with minimum Effective Series Inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.

Each circuit should be placed as close as possible to the specific AV_{DD} pin being supplied to minimize noise coupled from nearby circuits. It should be possible to route directly from the capacitors to the AV_{DD} pin, which is on the periphery of the 783 FC-PBGA footprint, without the inductance of vias.

Figure 49 shows the PLL power supply filter circuit.

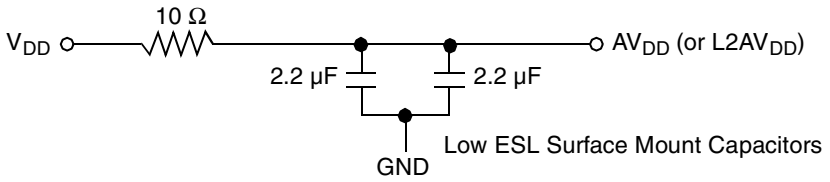


Figure 49. PLL Power Supply Filter Circuit

17.3 Decoupling Recommendations

Due to large address and data buses, and high operating frequencies, the MPC8541E can generate transient power surges and high frequency noise in its power supply, especially while driving large capacitive loads. This noise must be prevented from reaching other components in the MPC8541E system, and the MPC8541E itself requires a clean, tightly regulated source of power. Therefore, it is recommended that the system designer place at least one decoupling capacitor at each V_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} pins of the MPC8541E. These decoupling capacitors should receive their power from separate V_{DD}, OV_{DD}, GV_{DD}, LV_{DD}, and GND power planes in the PCB, utilizing short traces to minimize inductance. Capacitors may be placed directly under the device using a standard escape pattern. Others may surround the part.

These capacitors should have a value of 0.01 or 0.1 µF. Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the V_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors should have a low ESR (equivalent series resistance) rating to ensure the quick response time necessary. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors—100–330 µF (AVX TPS tantalum or Sanyo OSCON).

17.4 Connection Recommendations

To ensure reliable operation, it is highly recommended to connect unused inputs to an appropriate signal level. Unused active low inputs should be tied to OV_{DD}, GV_{DD}, or LV_{DD} as required. Unused active high inputs should be connected to GND. All NC (no-connect) signals must remain unconnected.

Power and ground connections must be made to all external V_{DD}, GV_{DD}, LV_{DD}, OV_{DD}, and GND pins of the MPC8541E.

17.5 Output Buffer DC Impedance

The MPC8541E drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I^2C).

To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to OV_{DD} or GND. Then, the value of each resistor is varied until the pad voltage is $OV_{DD}/2$ (see Figure 50). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices.

18 Document Revision History

Table 51 provides a revision history for this hardware specification.

Table 51. Document Revision History

Rev. No.	Date	Substantive Change(s)
4.2	1/2008	Added “Note: Rise/Fall Time on CPM Input Pins” and following note text to Section 10.2, “CPM AC Timing Specifications.”
4.1	07/2007	Inserted Figure 3, ““Maximum AC Waveforms on PCI interface for 3.3-V Signaling.”
4	12/2006	Updated Section 2.1.2, “Power Sequencing.” Updated back page information.
3.2	11/2006	Updated Section 2.1.2, “Power Sequencing.” Replaced Section 17.8, “JTAG Configuration Signals.”
3.1	10/2005	Table 4: Added footnote 2 about junction temperature. Table 4: Added max. power values for 1000 MHz core frequency. Removed Figure 3, “Maximum AC Waveforms on PCI Interface for 3.3-V Signaling.” Table 30: Modified note to $t_{LBKSKEW}$ from 8 to 9 Table 30: Changed $t_{LBKHOZ1}$ and $t_{LBKHOV2}$ values. Table 30: Added note 3 to $t_{LBKHOV1}$. Table 30 and Table 31: Modified note 3. Table 31: Added note 3 to $t_{LBKLOV1}$. Table 31: Modified values for t_{LBKHKT}, $t_{LBKLOV1}$, $t_{LBKLOV2}$, $t_{LBKLOV3}$, $t_{LBKLOZ1}$, and $t_{LBKLOZ2}$. Figure 21: Changed Input Signals: LAD[0:31]/LDP[0:3]. Table 43: Modified note for signal CLK_OUT. Table 43: PCI1_CLK and PCI2_CLK changed from I/O to I. Table 52: Added column for Encryption Acceleration.
3	8/29/2005	Table 4: Modified max. power values. Table 43: Modified notes for signals TSEC1_TXD[3:0], TSEC2_TXD[3:0], TRIG_OUT/READY, MSRCID4, and MDVAL.
2	8/2005	Previous revision’s history listed incorrect cross references. Table 2 is now correctly listed as Table 27 and Table 31 is now listed as Table 31. Table 7: Added note 2. Table 14: Modified min and max values for t_{DDKHMP}
1	6/2005	Table 27: Changed LV_{dd} to OV_{dd} for the supply voltage Ethernet management interface. Table 4: Modified footnote 4 and changed typical power for the 1000MHz core frequency. Table 31: Corrected symbols for body rows 9–15, effectively changing them from a high state to a low state.
0	6/2005	Initial Release.